



11/B 2813
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **Kenji MARUYAMA et al.**

Group Art Unit: 2813

Serial No.: 09/960,296 ✓

Examiner: L. Schillinger

Filed: September 24, 2001 ✓

P.T.O. Confirmation No.: 4754

For: **SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE SAME**

AMENDMENT UNDER 37 C.F.R. §1.111

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

July 14, 2003

Sir:

In response to the Office Action dated April 14, 2003, please amend the above-identified application as follows:

IN THE CLAIMS:

✓
Please cancel claims 4-6 without prejudice or disclaimer.

Please amend claims 1, 7, 8, 9 and 16 as follows:

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B'
1. (Twice Amended) A semiconductor device comprising a first electrode of a metal, a ferroelectric film formed above the first electrode, and a second electrode of a metal formed above the ferroelectric film, at least one of the first electrode and the second electrode being an electrode of a base metal, further comprising

an intermediate layer of perovskite crystal structure formed between the electrode of the base metal and the ferroelectric film, materials of the intermediate layer being different from materials of the first electrode, the second electrode and the ferroelectric film.